

Comparative Study on the Impacts of Anhydrous and Hydrus H₂O₂ on ALD Hafnium Oxide Growth on Titanium Nitride Surface

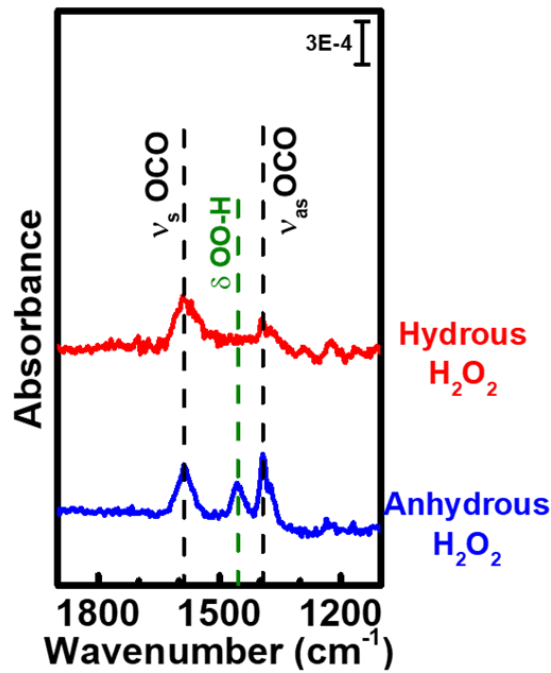


Figure 1. *in-situ* IR spectra, between 1100 cm⁻¹ and 1900 cm⁻¹, of hydrous and anhydrous H₂O₂ with reference to the TDMA-Hf modified TiN surface.

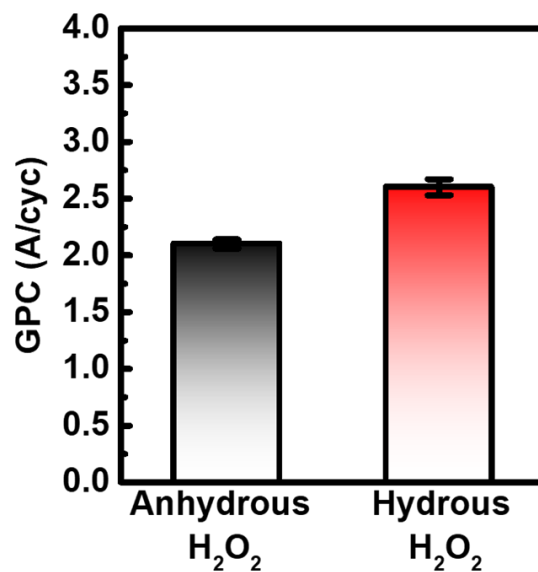


Figure 2. The growth per cycle (GPC) of HfO₂ thin films achieved using anhydrous and hydrous H₂O₂ as the oxidant source.